

N-channel 25 V 2.8 m Ω logic level MOSFET in LFPAK33 using NextPower Technology

Rev. 3 — 15 June 2012

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	$T_j = 25$ °C	-	-	25	V
drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u> _	-	70	Α
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	88	W
junction temperature		-55	-	175	°C
eristics					
drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 10	-	3.25	3.75	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 10</u>	-	2.45	2.8	mΩ
acteristics					
gate-drain charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 12.5 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	3.9	-	nC
total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 12.5 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	16.3	-	nC
	drain-source voltage drain current total power dissipation junction temperature eristics drain-source on-state resistance acteristics gate-drain charge	drain-source voltage $T_j = 25^{\circ}\text{C}$ drain current $T_{mb} = 25^{\circ}\text{C}$; $V_{GS} = 10 \text{ V}$; see Figure 1 total power dissipation $T_{mb} = 25^{\circ}\text{C}$; see Figure 2 junction temperature eristics drain-source on-state resistance $V_{GS} = 4.5 \text{ V}$; $I_D = 25 \text{ A}$; $I_D = 25 \text{ C}$; see Figure 10 $V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $I_D = 25 \text{ A}$; $I_D = 25 \text{ C}$; see Figure 10 acteristics gate-drain charge $V_{GS} = 4.5 \text{ V}$; $I_D = 25 \text{ A}$; $V_{DS} = 12.5 \text{ V}$; see Figure 12; see Figure 13 total gate charge $V_{GS} = 4.5 \text{ V}$; $I_D = 25 \text{ A}$; $V_{DS} = 12.5 \text{ V}$;	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		B
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT1210 (LFPAK33)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R8-25MLC	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25^{\circ}C$	-	25	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u> -	70	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u> -	70	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4	-	536	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	88	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	350	-	V
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	<u>[1]</u> _	70	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	536	Α
Avalanche ru	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 70 A; $V_{sup} \le$ 25 V; R_{GS} = 50 Ω; unclamped; see Figure 3	-	77	mJ

^[1] Continuous current is limited by package.

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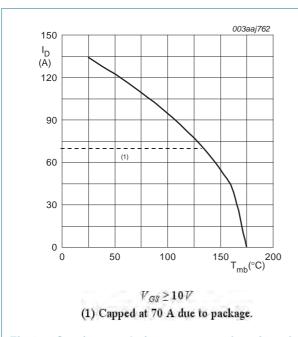


Fig 1. Continuous drain current as a function of mounting base temperature

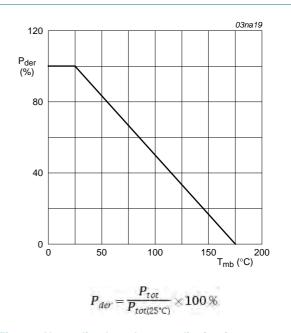


Fig 2. Normalized total power dissipation as a function of mounting base temperature

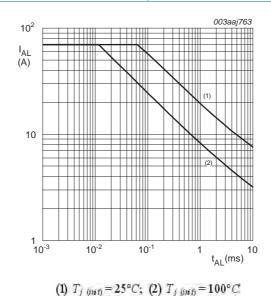
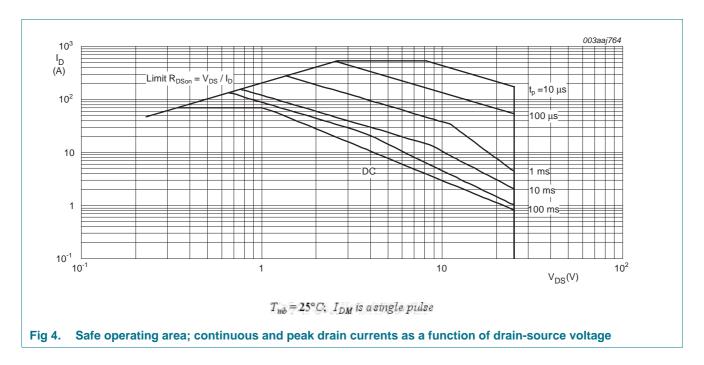


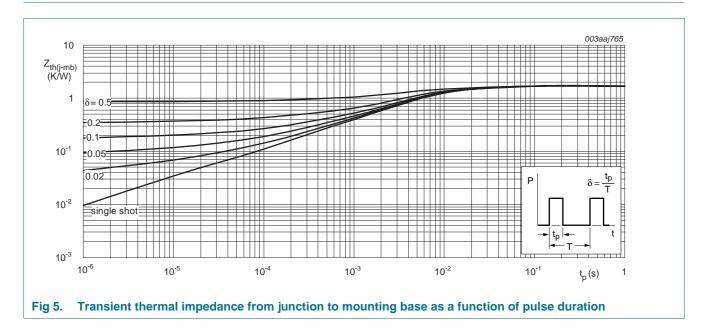
Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	1.49	1.7	K/W



6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	25	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.45	1.74	2.15	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature		-	-4.2	-	mV/K
I _{DSS}	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 10</u>	-	3.25	3.75	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ °C};$ see Figure 10; see Figure 11	-	-	6	mΩ
		V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 25 °C; see <u>Figure 10</u>	-	2.45	2.8	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	4.5	mΩ
R _G	gate resistance	f = 1 MHz	0.37	0.74	1.48	Ω
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 12.5 V; V _{GS} = 10 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	37.7	-	nC
		I_D = 25 A; V_{DS} = 12.5 V; V_{GS} = 4.5 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	16.3	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	36.7	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}$; $V_{DS} = 12.5 \text{ V}$; $V_{GS} = 4.5 \text{ V}$;	-	6.5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 12; see Figure 13	-	3.9	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.6	-	nC
Q_{GD}	gate-drain charge		-	3.9	-	nC
V _{GS(pl)}	gate-source plateau voltage	I_D = 25 A; V_{DS} = 12.5 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	2.9	-	V
C _{iss}	input capacitance	V _{DS} = 12.5 V; V _{GS} = 0 V; f = 1 MHz;	-	2432	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	533	-	pF
C _{rss}	reverse transfer capacitance		-	198	-	pF

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	$V_{DS} = 12.5 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	16.4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	24.6	-	ns
t _{d(off)}	turn-off delay time		-	19.9	-	ns
t _f	fall time		-	13.1	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12.5 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	14.3	-	nC
Source-drai	in diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 15</u>	-	0.82	1.1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	21.3	-	ns
Qr	recovered charge	V _{DS} = 12.5 V	-	14.1	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{DS} = 12.5 \text{ V; see } \frac{\text{Figure } 16}{\text{Miss}}$	-	12.1	-	ns
t _b	reverse recovery fall time		-	9.2	-	ns

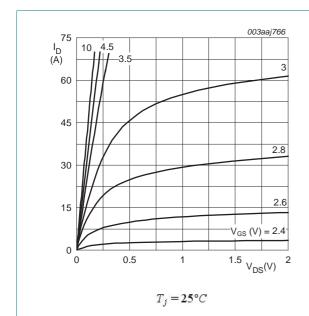


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

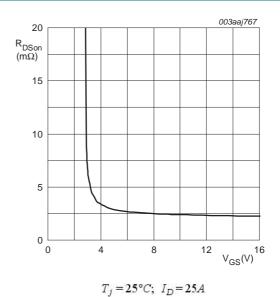


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

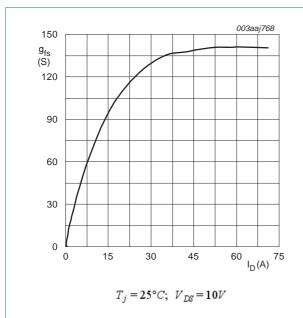


Fig 8. Forward transconductance as a function of drain current; typical values

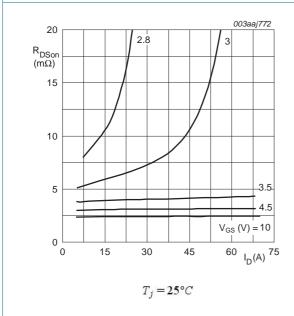


Fig 10. Drain-source on-state resistance as a function of drain current; typical values

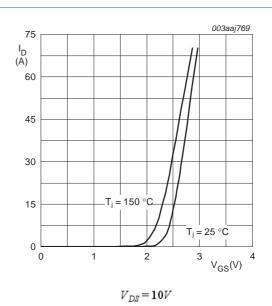


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

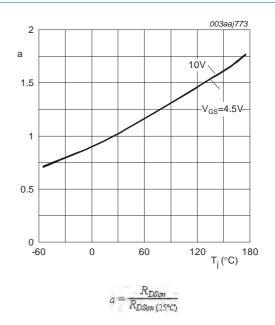


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

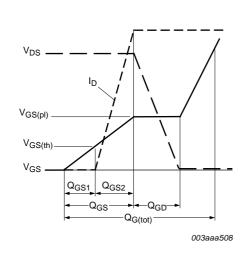


Fig 12. Gate charge waveform definitions

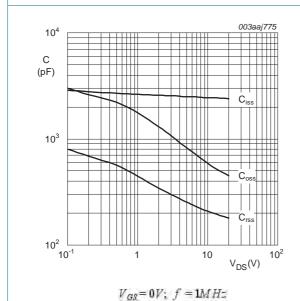
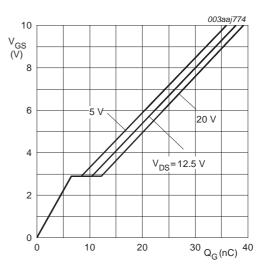


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 13. Gate-source voltage as a function of gate charge; typical values

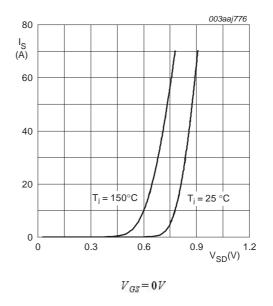
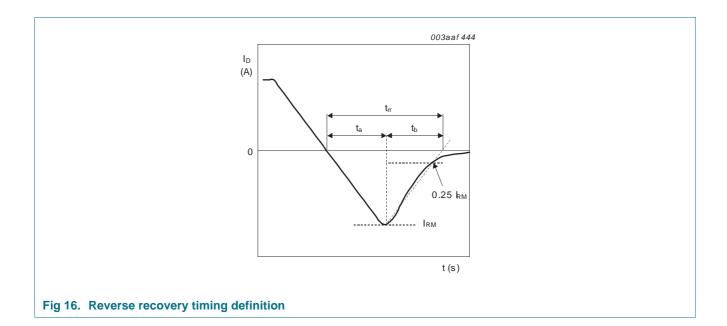


Fig 15. Source current as a function of source-drain voltage; typical values



7. Package outline

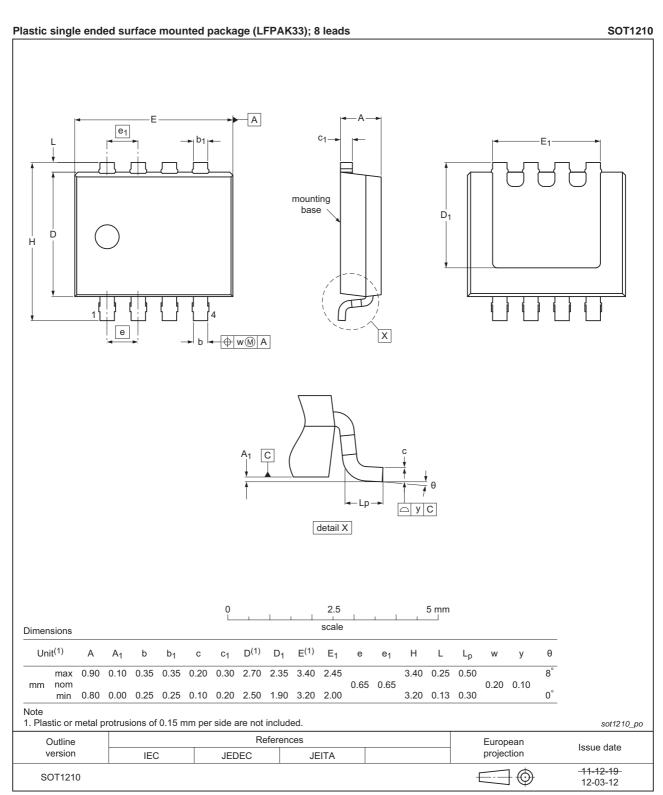


Fig 17. Package outline SOT1210 (LFPAK33)

PSMN2R8-25MLC

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N-channel 25 V 2.8 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R8-25MLC v.3	20120615	Product data sheet	-	PSMN2R8-25MLC v.2
Modifications:	 Various changes to 	content.		
PSMN2R8-25MLC v.2	20120607	Product data sheet	-	PSMN2R8-25MLC v.1

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9. Legal information

9.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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